Microelectronics Circuit Analysis and Design

Donald A. Neamen

Chapter 5

The Bipolar Junction Transistor

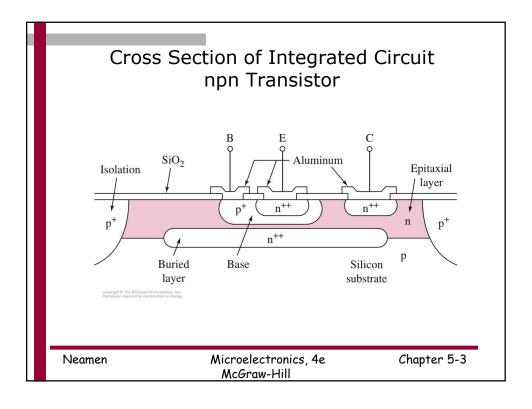
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In this chapter, we will:

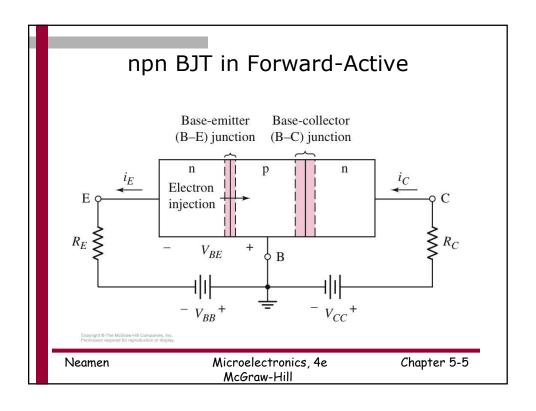
- □ Discuss the physical structure and operation of the bipolar junction transistor.
- □ Understand the dc analysis and design techniques of bipolar transistor circuits.
- Examine three basic applications of bipolar transistor circuits.
- □ Investigate various dc biasing schemes of bipolar transistor circuits, including integrated circuit biasing.
- Consider the dc biasing of multistage or multitransistor circuits.

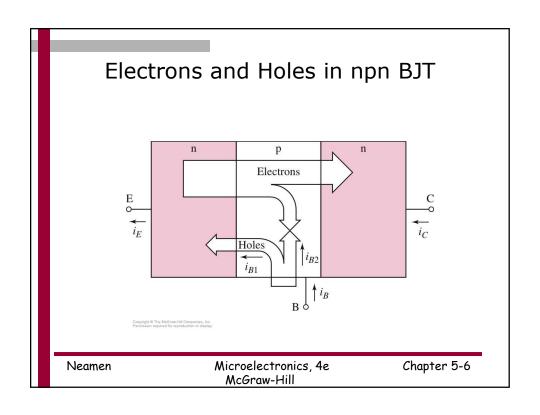
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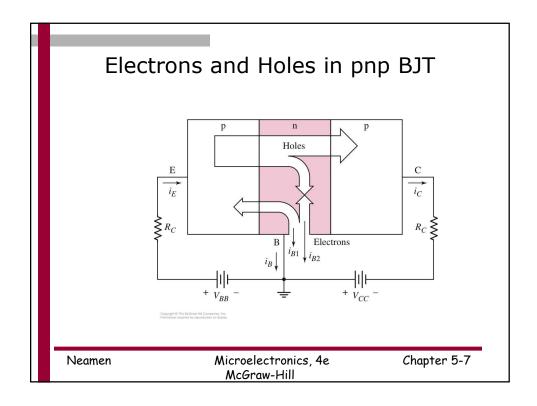
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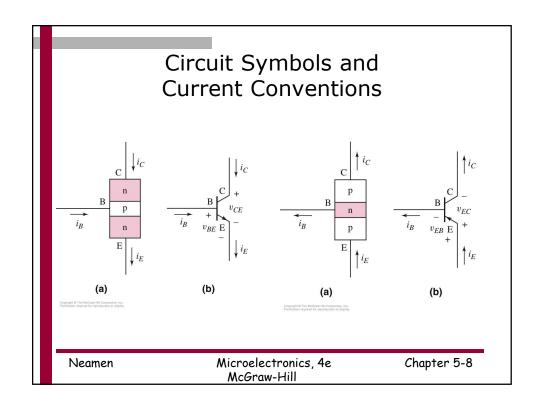


Modes of Operation Forward-Active B-E junction is forward biased B-C junction is reverse biased Saturation B-E and B-C junctions are forward biased Cut-Off B-E and B-C junctions are reverse biased Inverse-Active (or Reverse-Active) B-E junction is reverse biased B-C junction is forward biased









Current Relationships

$$i_{E} = i_{C} + i_{B}$$

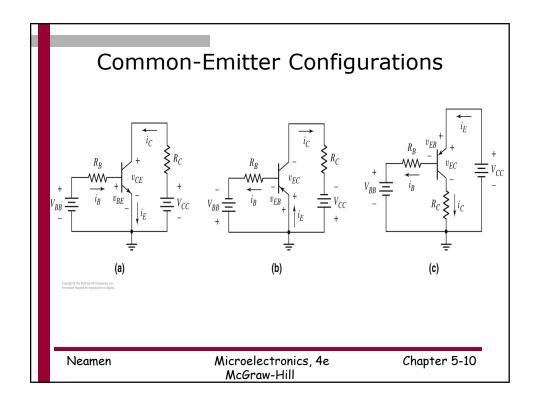
$$i_{C} = \beta i_{B}$$

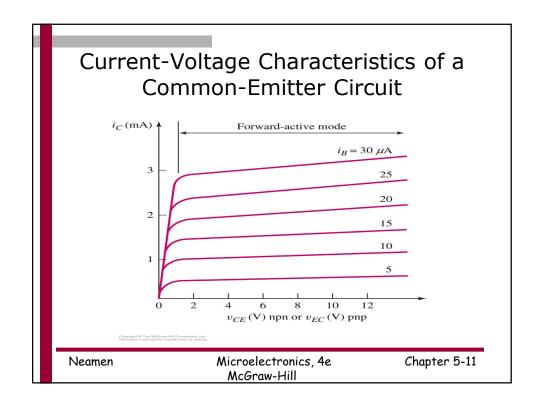
$$i_{E} = (1 + \beta i_{B})$$

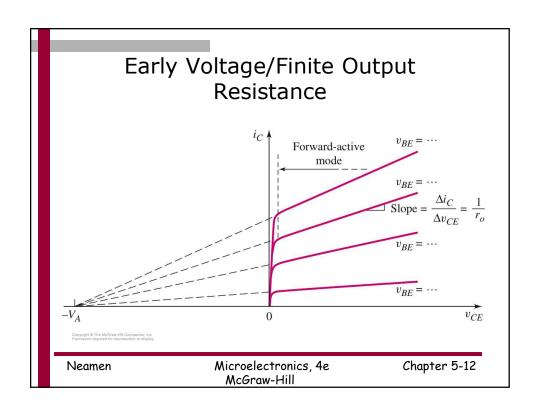
$$i_{C} = \alpha i_{E}$$

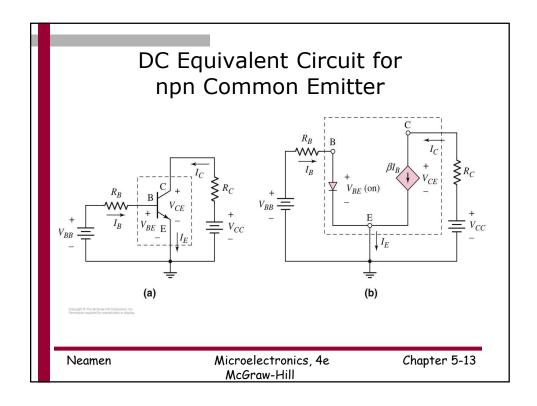
$$\beta = \frac{\alpha}{1 - \alpha}$$

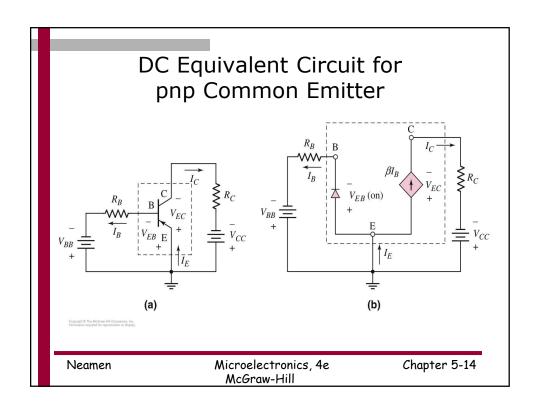
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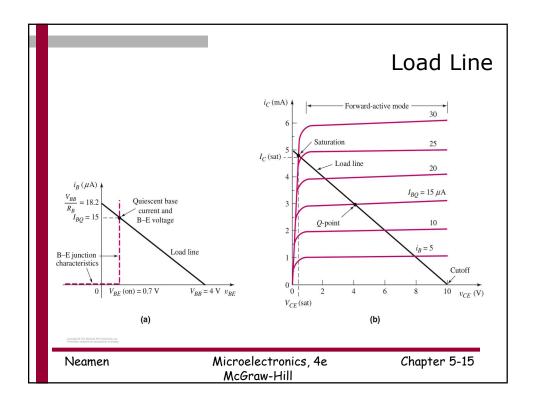












Problem-Solving Technique: Bipolar DC Analysis

- 1. Assume that the transistor is biased in forward active mode
 - a. $V_{BE} = V_{BE}(on)$, $I_B > 0$, & $I_C = \beta I_B$
- 2. Analyze 'linear' circuit.
- 3. Evaluate the resulting state of transistor.
 - a. If $V_{CE} > V_{CE}(sat)$, assumption is correct
 - b. If I_B < 0, transistor likely in cutoff
 - c. If V_{CE} < 0, transistor likely in saturation
- 4. If initial assumption is incorrect, make new assumption and return to Step 2.

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